

General Purpose Transistor NPN Silicon

MMBT3904LT1

ON Semiconductor Preferred Device

MAXIMUM RATINGS

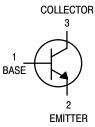
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	40	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	VEBO	6.0	Vdc
Collector Current — Continuous	IC	200	mAdc



CASE 318-08, STYLE 6 SOT-23 (TO-236)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board(1) $T_A = 25^{\circ}C$	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(2) T _A = 25°C	PD	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	TJ, T _{stg}	-55 to +150	°C



DEVICE MARKING

MMBT3904LT1 = 1AM

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (3) (I _C = 1.0 mAdc, I _B = 0)	V(BR)CEO	40	_	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V(BR)CBO	60	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V(BR)EBO	6.0	_	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	_	50	nAdc
Collector Cutoff Current (VCE = 30 Vdc, VEB = 3.0 Vdc)	ICEX	_	50	nAdc

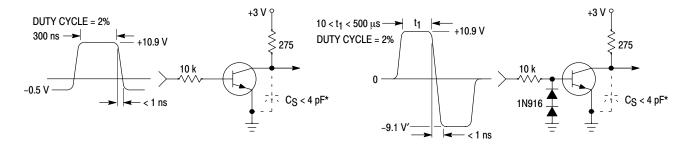
- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Charac	cteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(3)				1	•
DC Current Gain (1) (IC = 0.1 mAdc, VCE = 1.0 Vdc) (IC = 1.0 mAdc, VCE = 1.0 Vdc) (IC = 10 mAdc, VCE = 1.0 Vdc) (IC = 50 mAdc, VCE = 1.0 Vdc) (IC = 100 mAdc, VCE = 1.0 Vdc)		HFE	40 70 100 60 30	- 300 - -	_
Collector–Emitter Saturation Voltage (3) ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)		VCE(sat)		0.2 0.3	Vdc
Base–Emitter Saturation Voltage (3) (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 50 mAdc, IB = 5.0 mAdc)		V _{BE} (sat)	0.65 —	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTIC	S				
Current-Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 M	lHz)	fT	300	_	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	pF
Input Impedance (VCE = 10 Vdc, IC = 1.0 mAdc, f = 1.0 kg	Hz)	h _{ie}	1.0	10	k ohms
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kd	Hz)	h _{re}	0.5	8.0	X 10 ⁻⁴
Small–Signal Current Gain (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{fe}	100	400	_
Output Admittance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μ Adc, R _S = 1.	0 k ohms, f = 1.0 kHz)	NF	_	5.0	dB
SWITCHING CHARACTERISTICS		•		•	•
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	_	35	
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r		35	ns
Storage Time	(V _{CC} = 3.0 Vdc,	t _S		200	ne
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f	_	50	ns

^{3.} Pulse Test: Pulse Width \leq 300 $\mu\text{s},$ Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

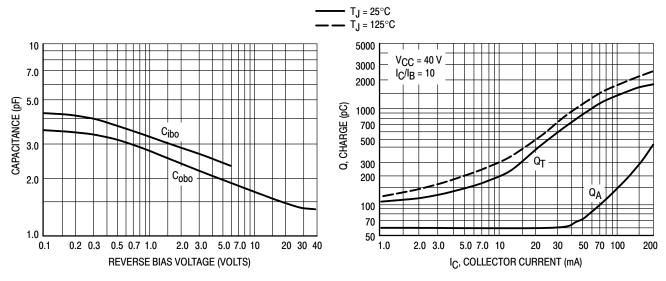
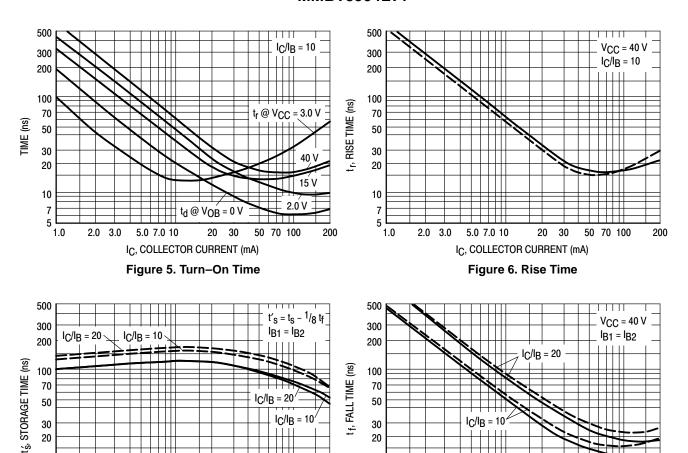


Figure 3. Capacitance

Figure 4. Charge Data



I_C, COLLECTOR CURRENT (mA)

Figure 7. Storage Time

5.0 7.0 10

10

1.0

2.0 3.0

I_C, COLLECTOR CURRENT (mA)

Figure 8. Fall Time

200

5.0 7.0 10

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

200

10

1.0

2.0

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth} = 1.0 \text{ Hz})$

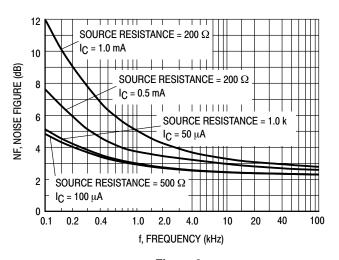


Figure 9.

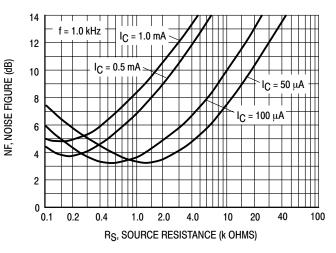


Figure 10.

h PARAMETERS

 $(VCE = 10 Vdc, f = 1.0 kHz, TA = 25^{\circ}C)$

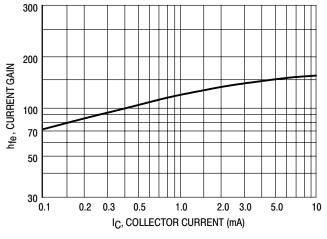
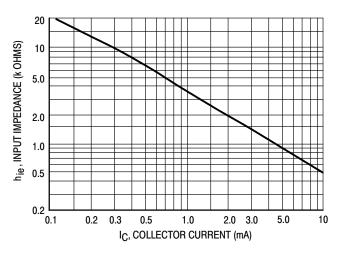


Figure 11. Current Gain

Figure 12. Output Admittance



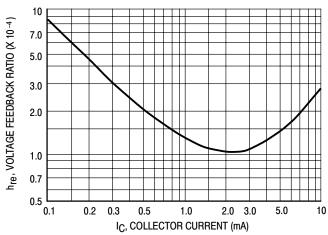


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

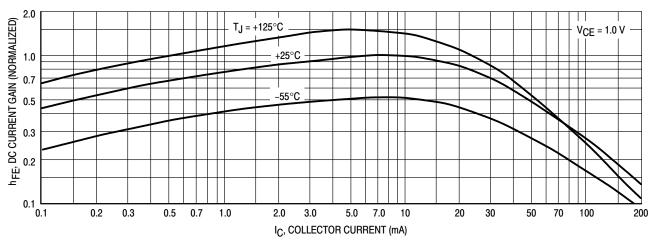


Figure 15. DC Current Gain

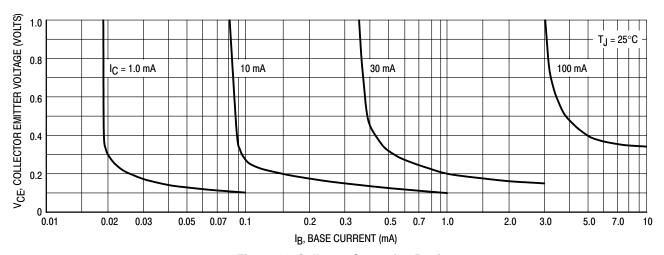
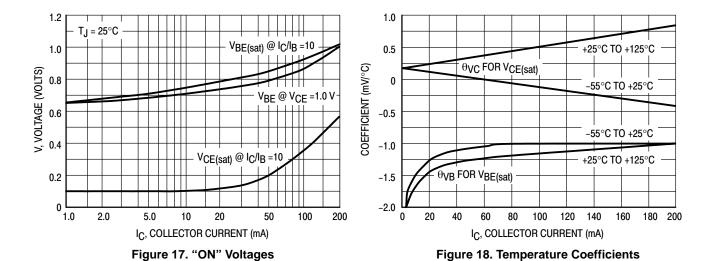


Figure 16. Collector Saturation Region

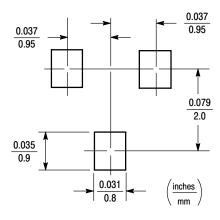


INFORMATION FOR USING THE SOT-23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-23

SOT-23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SOT–23 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT-23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT-23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

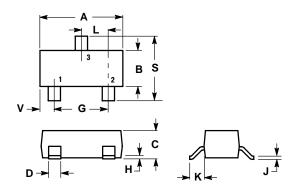
SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes.
 Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.
- * Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AF



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	INCHES MILLIMETE		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
7	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

STYLE 6:

PIN 1. BASE

- 2. EMITTER
- 3. COLLECTOR

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